



(Standard type





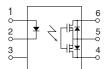
E PhotoMOS



Panasonic ideas for life

8.8 252 3.9 3.9 154 8.8 252 3.9 154

mm inch



FEATURES

1. 60V type couples high capacity (0.55A) with low on-resistance (1 Ω).

GU-E					
(1 Form B type) type					
AQV410EH	AQV412EH				
350V	60V				
0.13A	0.55A				
511.511					
18Ω	1Ω				
	(1 Form B AQV410EH 350V 0.13A				

General use and economy type. DIP (1 Form B) 6-pin type. Reinforced insulation 5,000V type.

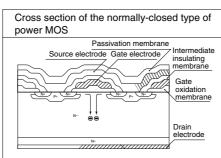
2. This is the low-cost version PhotoMOS 1 Form B output type relay.

Compared to the previous GU PhotoMOS 1 Form B type relay, the attainment of an economical price that is approximately 22% lower will further broaden its market.

3. Normally closed type (2 Form B) is low on-resistance.

(All AQO4 PhotoMOS are Form B types. And also the Form A types have a low on-resistance.)

This has been realized thanks to the built-in MOSFET processed by our proprietary method, DSD (Doublediffused and Selective Doping) method.



4. Controls low-level analog signals PhotoMOS relays feature extremely low closed-circuit offset voltage to enable control of low-level analog signals without distortion.

5. High sensitivity, low ON resistance

Can control a maximum 0.13 A load current with a 5 mA input current. Low ON resistance of 18 Ω (AQV410EH). Stable operation because there are no metallic contact parts.

6. Low-level off-state leakage current

The SSR has an off-state leakage current of several milliamperes, whereas the PhotoMOS relay has typ. 100 pA even with the rated load voltage of 400 V (AQV414E).

7. Reinforced insulation 5,000 V type also available.

More than 0.4 mm internal insulation distance between inputs and outputs. Conforms to EN41003, EN60950 (reinforced insulation).

TYPICAL APPLICATIONS

- Power supply
- Measuring equipment
- · Security equipment
- Telephone equipment
- Sensors

TYPES

Туре	I/O isolation voltage				Pa				
		Output rating*		Through hole terminal	Sı	Packing quantity			
			Lood			Tape and reel	packing style		Tape and reel
		Load voltage	Load	Tube pac	king style	Picked from the 1/2/3-pin side	Picked from the 4/5/6-pin side	Tube	
AC/DC type	1,500 V AC (Standard)	400 V	120 mA	AQV414E	AQV414EA	AQV414EAX	AQV414EAZ	1 tube contains	1,000 pcs.
	5,000 V AC (Reinforced)	60 V	550 mA	AQV412EH	AQV412EHA	AQV412EHAX	AQV412EHAZ	50 pcs. 1 batch contains	
		350 V	350 V 130 mA AQ\		AQV410EHA	AQV410EHAX	AQV410EHAZ	500 pcs.	
		400 V	120 mA	AQV414EH	AQV414EHA	AQV414EHAX	AQV414EHAZ	333 poo.	1

^{*}Indicate the peak AC and DC values.

Note: For space reasons, the SMD terminal shape indicator "A" and the package style indicator "X" or "Z" are not marked on the relay.

GU-E PhotoMOS (AQV414E, AQV41OEH)

RATING

1. Absolute maximum ratings (Ambient temperature: 25°C 77°F)

	Item	Symbol	Type of connection	AQV414E(A)	AQV412EH(A)	AQV410EH(A)	AQV414EH(A)	Remarks	
	LED forward current	I F		50 mA					
Input	LED reverse voltage	V R		5 V					
	Peak forwrd current	IFP			1 A			f = 100 Hz, Duty factor = 0.1%	
	Power dissipation	Pin		75 mW					
	Load voltage (peak AC)	VL		400 V	60 V	350 V	400 V		
	Continuous load current	Iι	Α	0.12 A	0.55 A	0.13 A	0.12 A	A connection: Peak AC, DC B.C connection: DC	
			В	0.13 A	0.65 A	0.15 A	0.13 A		
Output			С	0.15 A	0.8 A	0.17 A	0.15 A	B,C connection. DC	
	Peak load current	Ipeak		0.3 A	1.5 A	0.4 A	0.3 A	A connection: 100 ms (1 shot), V _L = DC	
	Power dissipation	Pout		500 mW					
Total power dissipation		Р⊤		550 mW					
I/O isolation voltage		Viso		1,500 V AC 5,000 V AC					
Temperature limits	Operating	Topr		-40°C, to +85°C, -40°E to +185°E				Non-condensing at low temperatures	
	Storage	T _{stg}		-40°C to +100°C -40°F to +212°F					

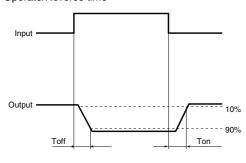
2. Electrical characteristics (Ambient temperature: 25°C 77°F)

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	Symbol	Type of connection	AQV414E(A)	AQV412EH(A)	AQV410EH(A)	AQV414EH(A)	Condition			
	LED operate (OFF) current		Typical	Foff	_	1.45 mA	1.9 mA	1.9 mA	1.9 mA	
la mari			Maximum			3.0 mA				I∟= Max.
	LED reverse (ON)		Minimum	1_		0.3 mA	0.4 mA	0.4 mA	0.4 mA	I Man
Input	current		Typical	Fon	-	1.40 mA	1.8 mA	1.8 mA	1.8 mA	IL= Max.
	I CD drana	t olto ao	Typical	VF		1.25 V (1.14 V at I _F = 5 mA)				I 50 A
	LED dropout voltage		Maximum	VF	_	1.5 V				I⊧= 50 mA
			Typical			26 Ω	1 Ω	18 Ω	25.2 Ω	I _F = 0 mA
	On resistance		Maximum	Ron	A	50 Ω	2.5 Ω	35 Ω	50 Ω	IL= Max. Within 1 s on time
			Typical	Ron	В	20 Ω	$0.55~\Omega$	13 Ω	19 Ω	I _F = 0 mA I _L = Max. Within 1 s on time
Output			Maximum			25 Ω	1.3 Ω	17.5 Ω	25 Ω	
·			Typical	Ron	С	10 Ω	0.3 Ω	6.5 Ω	10 Ω	I _F = 0 mA I _L = Max. Within 1 s on time
			Maximum			12.5 Ω	0.7 Ω	8.8 Ω	12.5 Ω	
	Off state leakage current		Maximum	Leak	_	1 μΑ	10 μΑ	10 μΑ	10 μΑ	I _F = 5 mA V _L = Max.
Transfer characteristics	Switching speed	Operate	Typical	Toff	_	0.7 ms	3 ms	1.5 ms	1.3 ms	$I_F = 0 \text{ mA} \rightarrow 5 \text{ mA}$ $I_L = \text{Max.}$ $I_F = 5 \text{ mA} \rightarrow 0 \text{ mA}$ $I_L = \text{Max.}$
		(OFF) time*	Maximum			2.0 ms	10 ms	3.0 ms	3.0 ms	
		Reverse (ON) time*	Typical	Ton	_	0.1 ms	0.3 ms	0.3 ms	0.3 ms	
			Maximum			1.0 ms	1.5 ms	1.5 ms	1.5 ms	
	I/O capacitance		Typical	Ciso	_	0.8 pF				f = 1 MHz V _B = 0 V
			Maximum	Ciso		1.5 pF				
	Initial I/O isolation resistance		Minimum	Riso	_	1,000 ΜΩ				500 V DC

Note: Recommendable LED forward current

Standard type $I_F = 5 \text{ mA}$ Reinforced type $I_F = 5 \text{ to } 10 \text{ mA}$

*Operate/Reverse time



- **■** For Dimensions.
- **■** For Schematic and Wiring Diagrams.
- **■** For Cautions for Use.

For type of connection.